

High-current gain Power Transistor (60V, 3A)

2SD2318/2SD1944

●Features

- 1) High DC current gain.
- 2) Low saturation voltage, typically $V_{CE(sat)} = 0.5V$ at $I_C / I_B = 2A / 0.5A$.
- 3) Complements the 2SB1639.

●Packaging specifications and h_{FE}

Type	2SD2318	2SD1944
Package	CPT3	TO-220FP
h _{FE}	UV	HJK
Code	TL	—
Basic ordering unit (pieces)	2500	500

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	V _{CBO}	80	V	
Collector-emitter voltage	V _{CEO}	60	V	
Emitter-base voltage	V _{EBO}	6	V	
Collector current	I _C	3 4.5	A A (Pulse) *	
Collector power dissipation	2SD2318 2SD1944	P _C	1 15 2 30	W (T _c =25°C) W (T _c =28°C)
Junction temperature	T _J	150	°C	
Storage temperature	T _{STG}	-55~+150	°C	

* Single pulse P_w=100ms**●Electrical characteristics (Ta=25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	80	—	—	V	I _C =50 μA
Collector-emitter breakdown voltage	BV _{CEO}	60	—	—	V	I _C =1mA
Emitter-base breakdown voltage	BV _{EBO}	6	—	—	V	I _E =50 μA
Collector cutoff current	I _{CEO}	—	—	100	μA	V _{CB} =80V
Emitter cutoff current	I _{EBO}	—	—	100	μA	V _{EB} =6V
Collector-emitter saturation voltage	V _{CE(sat)}	—	—	1.0	V	I _C /I _B =2A/0.05A
Base-emitter saturation voltage	V _{BE(sat)}	—	—	1.5	V	I _C /I _B =2A/0.05A
DC current transfer ratio	2SD2318 2SD1944	560 400	—	1800 2000	—	V _{CE} /I _C =4V/0.5A
Transition frequency	f _T	—	50	—	MHz	V _{CE} =5V, I _E =-0.2A, f=10MHz
Output capacitance	C _{OB}	—	60	—	pF	V _{CE} =10V, I _E =0A, f=1MHz

* Measured using pulse current.

(96-244-D302)